



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on)	I _D Tc = +25°C	
68V	$8.0 \text{m}\Omega$ @ V _{GS} = 10V	100A	

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

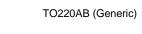
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

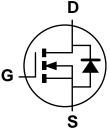
- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (2)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)











Equivalent Circuit



Pin Out Configuration

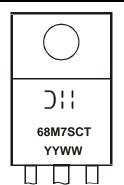
Ordering Information (Note 4)

Part Number		Case	Packaging	
	DMN68M7SCT	TO220AB (Generic)	50 Pieces/Tube	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Dil = Manufacturer's Marking
68M7SCT = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	68	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	ΙD	100 80	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	400	Α		
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	400	Α
Maximum Continuous Body Diode Forward Current (Note 5)			Is	100	Α
Avalanche Current (Note 6) L = 0.3mH			las	35	А
Avalanche Energy (Note 6) L = 0.3mH			Eas	183	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) $ T_{C} = +25^{\circ}C $ $ T_{C} = +70^{\circ}C $	l Ph	125 80	W
Thermal Resistance, Junction to Case (Note 5)	Rejc	1.0	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	68	_		V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	1	_	1	μΑ	V _{DS} = 68V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	Vgs(TH)	1.3	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	RDS(ON)		6.2	8.0	mΩ	Vgs = 10V, ID = 20A	
Diode Forward Voltage	VsD	_	0.7	1.2	V	V _G S = 0V, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	l	4260	1		V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss		430	-	pF		
Reverse Transfer Capacitance	Crss	_	198	_			
Gate Resistance	Rg	_	1.75	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	72.9	_		V _{DD} = 30V, I _D = 20A	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	36.0	_			
Gate-Source Charge	Qgs	_	8.0	_	nC		
Gate-Drain Charge	Q _{GD}	_	15.3	_			
Turn-On Delay Time	tD(ON)	_	6.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $R_{G} = 1\Omega, I_{D} = 20A$	
Turn-On Rise Time	tR		18	_			
Turn-Off Delay Time	t _{D(OFF)}		36	_	ns		
Turn-Off Fall Time	tF	_	9.7	_			
Reverse Recovery Time	trr		31.4	_	ns	1 00A 11/14 400A/c-	
Reverse Recovery Charge	Q _{RR}	-	30.1	_	nC	$I_F = 20A$, di/dt = 100A/ μ s	

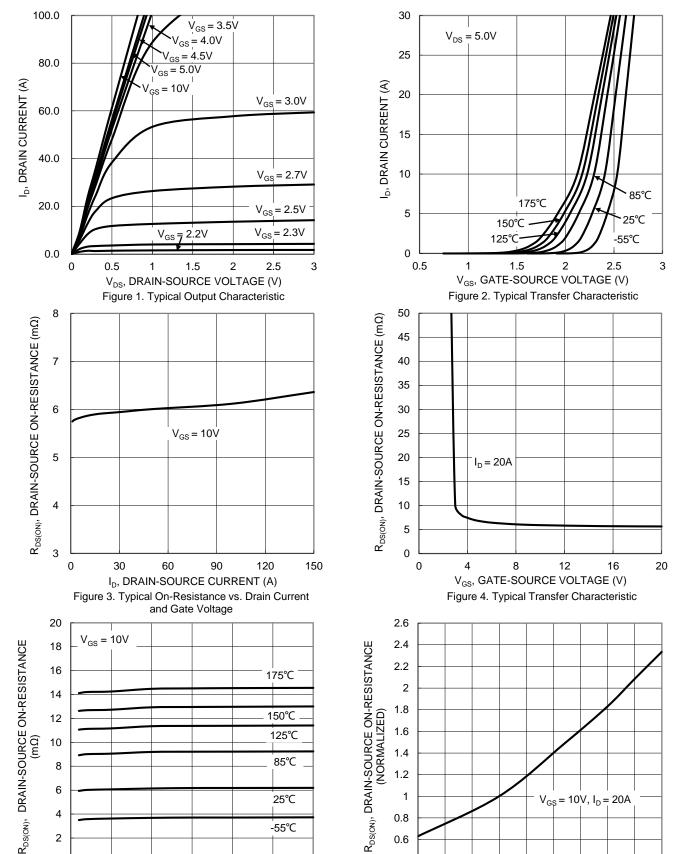
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Notes:

- 5. Device mounted on infinite heatsink.
- 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature

15

20

10

75

50

25

 $V_{GS} = 10V, I_D = 20A$

6

4

2

0

0

25°C

-55°C

30

25

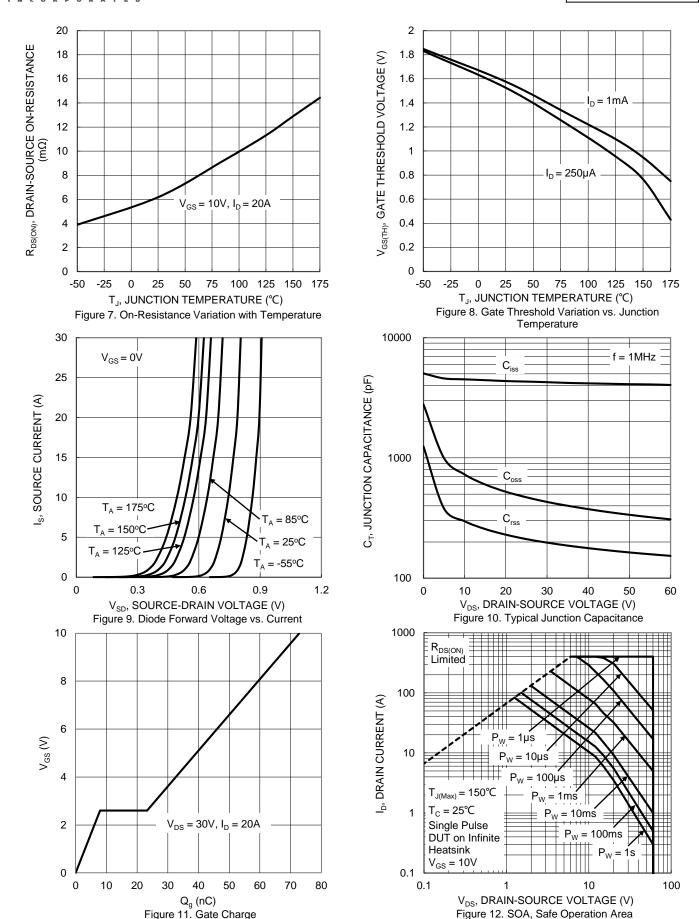
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0.8

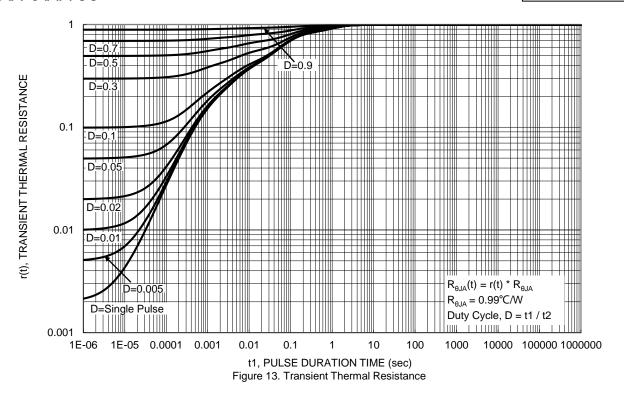
0.6 0.4

-50 -25 0 100 125 150 175







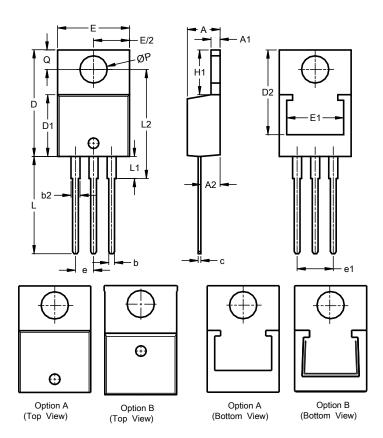




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB (Generic)



TO220AB (Generic)					
Dim	Min	Max	Тур		
A	3.56	4.82	-		
A1	0.51	1.39	-		
A2	2.04	2.92	-		
b	0.39	1.01	0.81		
b2	1.15	1.77	1.24		
C	0.356	0.61	-		
D	14.22	16.51	-		
D1	8.39	9.01	-		
D2	11.45	12.87	-		
е	-	-	2.54		
e1	-	-	5.08		
Е	9.66	10.66	-		
E1	6.86	8.89	-		
H	5.85	6.85	-		
L	12.70	14.73	-		
L1	-	4.42	-		
L2	15.80	17.51	16.00		
Р	3.54	4.08	-		
ø	2.54	3.42	-		
All Dimensions in mm					



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